

STRAINED SILICON MUSTER HAVING IMPROVED THERMAL CONDUCTIVITY AND METHOD FOR ITS FABRICATION boventors: Jung-Suk Goo et al. Attomey. Romald Coslick - 039153-0676 FOLEY & LARDNER - (310) 277-2223 Sheet 2 of 7

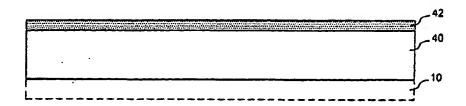


Figure 3a

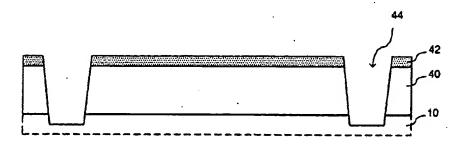
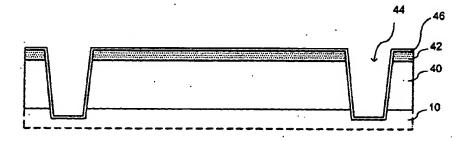


Figure 3b



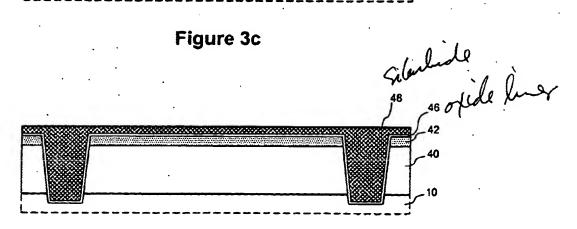


Figure 3d

STRAINED SILECON MOSFET HAVING IMPROVED THERMAL CONDUCTIVITY AND METHOD FOR ITS FABRICATION Inventors: Jung-Suk Goo et al.
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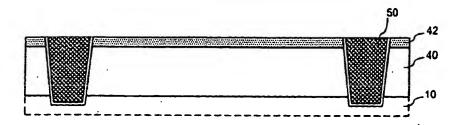


Figure 3e

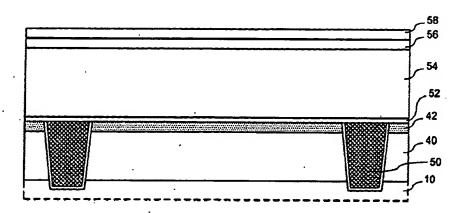


Figure 3f

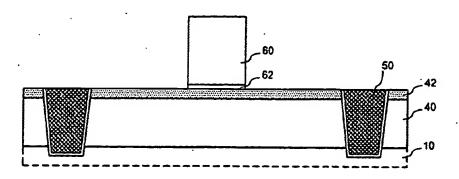


Figure 3g

STRAINED SILICON MOSFET HAV AU IMPROVED THERMAL CONDUCTIVITY AND METHOD FOR ITS FABRICATION Inventors: Jung-Suk Goo et al. Automey: Ronald Codick - 039153-0676 FOLEY & LARDNER - (310) 277-2223 Sheet 4 of 7

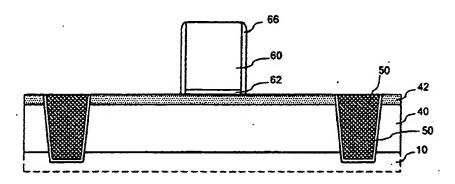


Figure 3h -

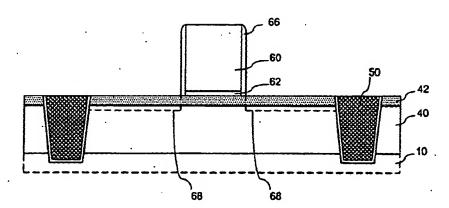


Figure 3i

STRAINED SILICON MOSFET HAVING IMPROVED THERMAL CONDUCTIVITY AND METHOD FOR ITS FABRICATION Inventors: Jung-Suk Goos as. Attorney: Ronald Codies 4.039153-0676 FOLEY & LARDNER - (310) 277-2223 Sheet 5 of 7

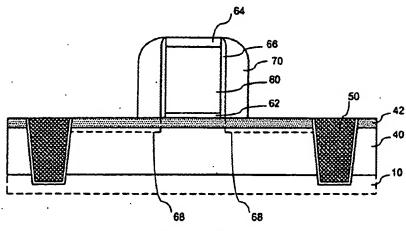


Figure 3j

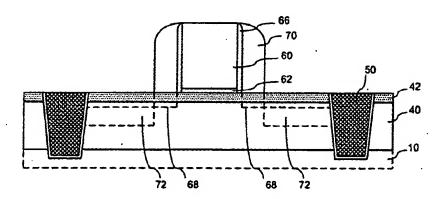


Figure 3k

STRAINED SILICON MOSFET HAVING IMPROVED THERMAL CONDUCTIVITY AND METHOD FOR ITS FABRICATION (INVENTED SUB-SUB-COST) SUB-COST (INVENTED SUB-COST) (

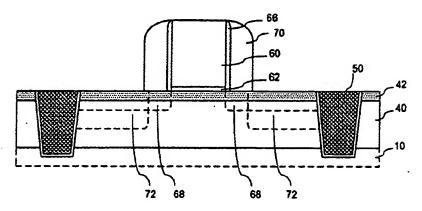


Figure 3L

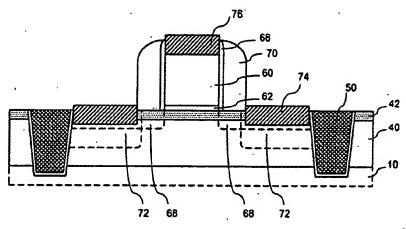


Figure 3m

STRAINED SILICON MOSFET HAVING IMPROVED THERMAL CONDUCTIVITY AND METHOD FOR ITS FABRICATION Inventors: Jung-Suk Goo et al. Attorney: Ronald Cotifick - 039153-0676 FOLEY & LARDNER - (310) 277-2223 Sheet 7 of 7

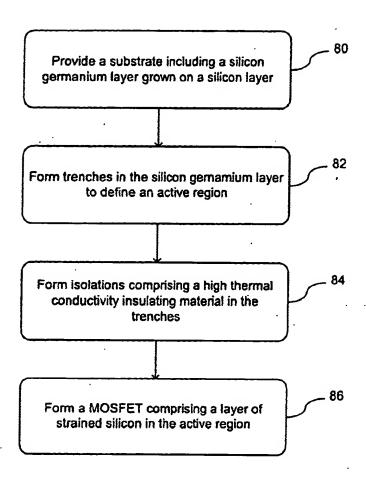


Figure 4